

1. Scope

The present specifications shall apply to an FMW-24H.

2. Outline

High Frequency Rectification

Type	Silicon Schottky Barrier Diode
Structure	Resin Molded
Applications	High Frequency Rectification

3. Flammability

UL94V-0(Equivalent)

4. Absolute maximum ratings

No.	Item	Symbol	Unit	Rating	Conditions
1	Transient Peak Reverse Voltage	V_{RSM}	V	40	
2	Peak Reverse Voltage	V_{RM}	V	40	
3	Average Forward Current	$I_{F(AV)}$	A	15	Refer to Derating of 7
4	Peak Surge Forward Current	I_{FSM}	A	120	Half sinewave, one shot
5	I^2t Limiting Value	I^2t	A^2s	75	$1msec \leq t \leq 10msec$
6	Junction Temperature	T_j	°C	-40 ~ +150	
7	Storage Temperature	T_{stg}	°C	-40 ~ +150	

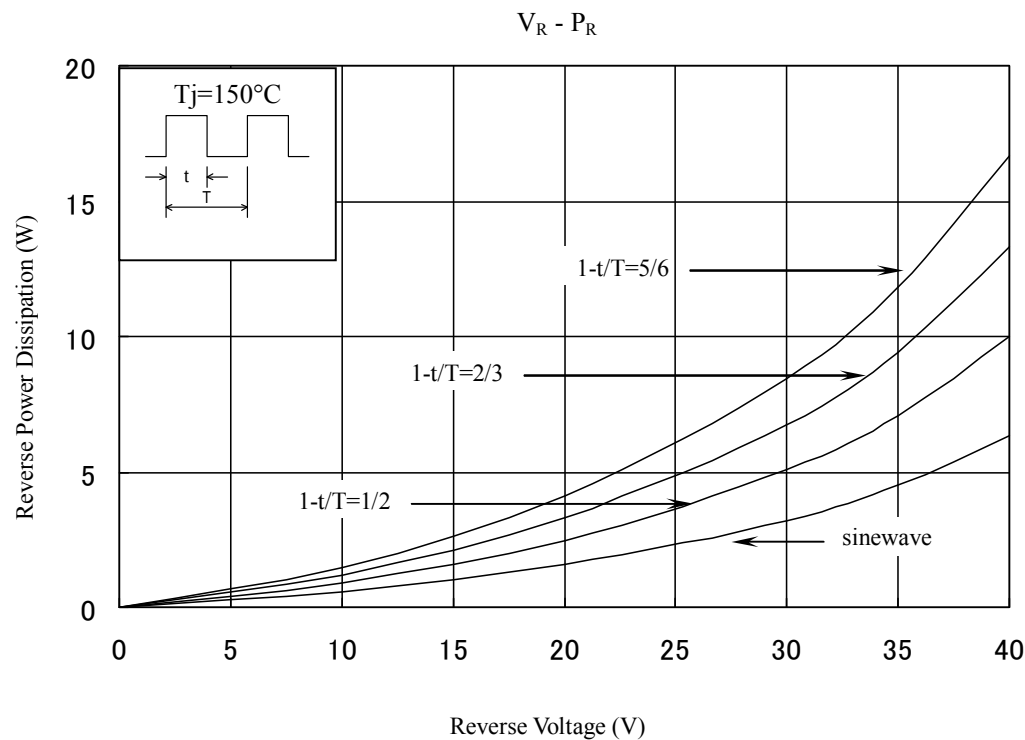
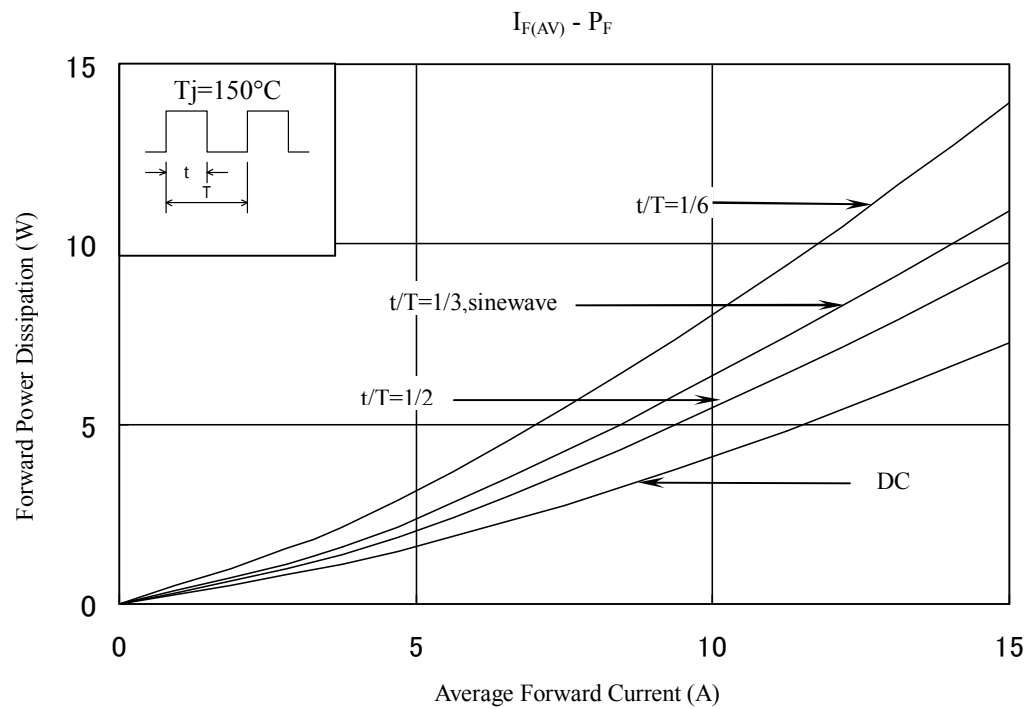
No.1,2,4&5 show ratings per one chip.

5. Electrical characteristics

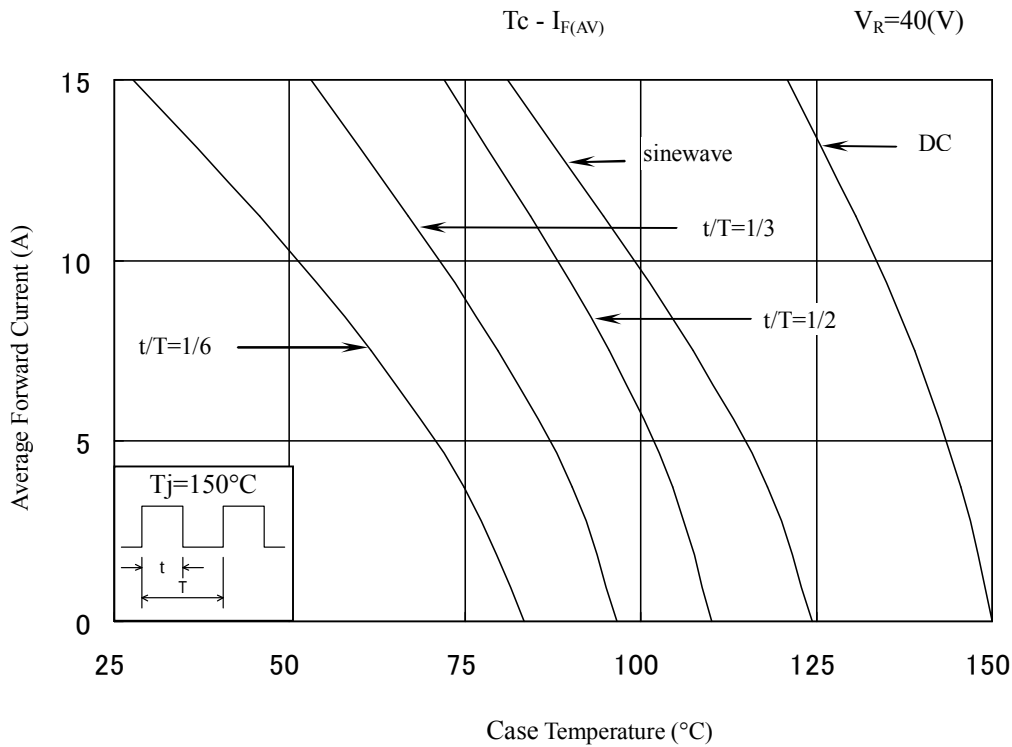
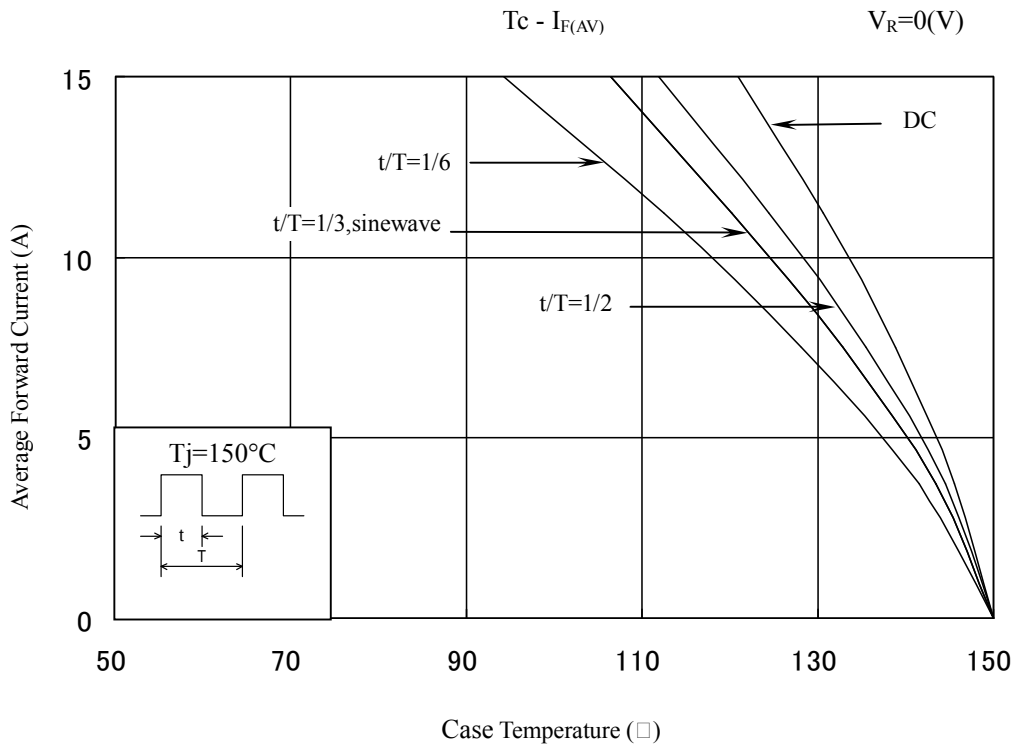
No.	Item	Symbol	Unit	Value	Conditions
1	Forward Voltage Drop	V_F	V	0.55 max.	$I_F=7.5A$
2	Reverse Leakage Current	I_R	mA	7.5 max.	$V_R=V_{RM}$
3	Reverse Leakage Current Under High Temperature	$H \cdot I_R$	mA	250 max.	$V_R=V_{RM}$, $T_j=150^\circ C$
4	Thermal Resistance	$R_{th(j-l)}$	°C/W	4.0 max.	Between Junction and case

No.1,2,&3 show characteristics per one chip.

6. Characteristics

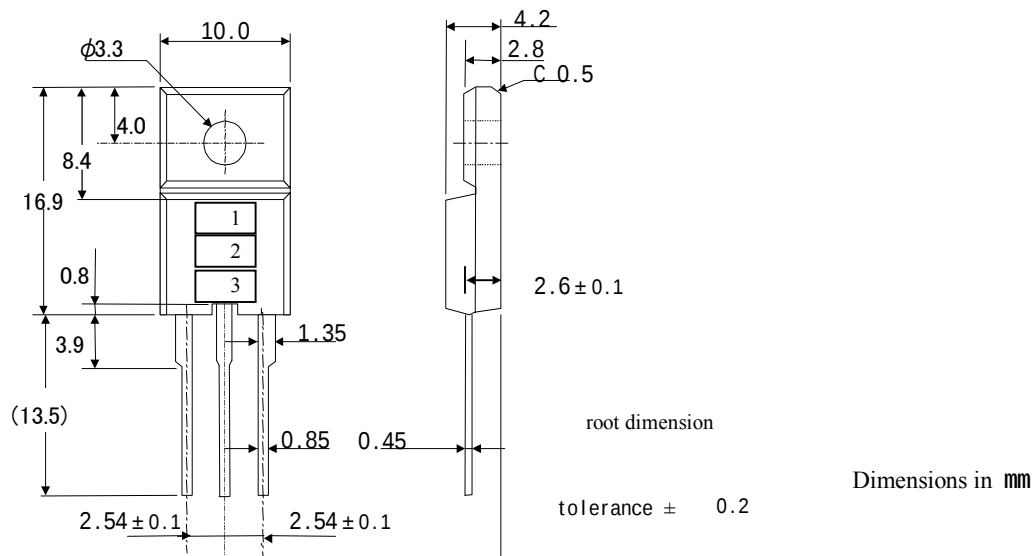


7. Derating



8. Package information

8-1Package type, physical dimensions and material



8-2Appearance

The body shall be clean and shall not bear any stain, rust or flaw.

8-3Marking

品名 Type Name	Marking		
	*1 Type Name	*2 Polarity	*3 Lot number
FMW-24H	FMW24H		1st letter: Last digit of year 2nd letter: Month From 1 to 9 for Jan. to Sep., O for Oct., N for Nov., D for Dec. 3rd & 4th letter: Day ex. 1718 (July. 17, 2001)